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R & T Code 4134005

Technical report No. 13

GROWTH AND CHARACTERIZATION OF THIN FILMS OF  $Y_2O_3$ ,  $La_2O_3$  AND  $La_2CuO_4$

by

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Prepared for Publication in

JOURNAL OF SOLID STATE CHEMISTRY

December 21, 1990

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## REPORT DOCUMENTATION PAGE

1a REPORT SECURITY CLASSIFICATION UNCLASSIFIED			1b RESTRICTIVE MARKINGS	
2a SECURITY CLASSIFICATION AUTHORITY			3 DISTRIBUTION / AVAILABILITY OF REPORT APPROVED FOR PUBLIC RELEASE DISTRIBUTION UNLIMITED	
2b DECLASSIFICATION / DOWNGRADING SCHEDULE				
4 PERFORMING ORGANIZATION REPORT NUMBER(S) REPORT NO. 13			5 MONITORING ORGANIZATION REPORT NUMBER(S) N000 14-89-J-1849	
6a NAME OF PERFORMING ORGANIZATION BROWN UNIVERSITY AARON WOLD		6b OFFICE SYMBOL (If applicable)		7a NAME OF MONITORING ORGANIZATION OFFICE OF NAVAL RESEARCH CODE 427 1113
6c ADDRESS (City, State, and ZIP Code) DEPARTMENT OF CHEMISTRY, BOX H BROWN UNIVERSITY PROVIDENCE, RI 02912			7b ADDRESS (City, State, and ZIP Code) DR. MARK ROSS 800 N. Quincy St. Arlington, VA 22217	
8a NAME OF FUNDING / SPONSORING ORGANIZATION		8b OFFICE SYMBOL (If applicable)		9 PROCUREMENT INSTRUMENT IDENTIFICATION NUMBER
8c ADDRESS (City, State, and ZIP Code)			10 SOURCE OF FUNDING NUMBERS	
			PROGRAM ELEMENT NO	PROJECT NO
			TASK NO	WORK UNIT NO
11 TITLE (Include Security Classification) GROWTH AND CHARACTERIZATION OF THIN FILMS OF $Y_2O_3$ , $La_2O_3$ AND $La_2CuO_4$				
12 PERSONAL AUTHOR(S) Y-M. Gao, P. Wu, K. Dwight and A. Wold				
13a. TYPE OF REPORT Technical		13b TIME COVERED FROM TO		14 DATE OF REPORT (Year, Month, Day) Dec 21, 1990
15 PAGE COUNT				
16 SUPPLEMENTARY NOTATION Prepared for publication in Journal of Solid State Chemistry				
17 COSATI CODES			18 SUBJECT TERMS (Continue on reverse if necessary; and identify by block number)	
FIELD	GROUP	SUB-GROUP		
19 ABSTRACT (Continue on reverse if necessary and identify by block number) $Y_2O_3$ , $La_2O_3$ and $La_2CuO_4$ films were prepared by an ultrasonic nebulization and pyrolysis method using acetylacetonates of the corresponding metals in alcohol solvents as source materials. Homogeneous, uniform films with good adherence have been obtained using this simple technique. As-deposited yttrium and lanthanum oxide films were poorly crystallized. After post-annealing in oxygen at higher temperature, they crystallized into cubic and hexagonal phases, respectively. Transparent yttrium and lanthanum oxide films have high electric breakdown voltages. Single phase polycrystalline $La_2CuO_4$ thin films were obtained from a source solution with a La:Cu ration of 2:1.				
20 DISTRIBUTION / AVAILABILITY OF ABSTRACT <input type="checkbox"/> UNCLASSIFIED/UNLIMITED <input type="checkbox"/> SAME AS RPT <input type="checkbox"/> DTIC USERS			21 ABSTRACT SECURITY CLASSIFICATION	
22a NAME OF RESPONSIBLE INDIVIDUAL			22b TELEPHONE (Include Area Code)	22c OFFICE SYMBOL

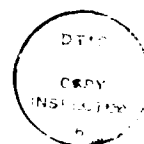
GROWTH AND CHARACTERIZATION OF THIN FILMS OF

$Y_2O_3$ ,  $La_2O_3$  AND  $La_2CuO_4$

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### Abstract

$\text{Y}_2\text{O}_3$ ,  $\text{La}_2\text{O}_3$  and  $\text{La}_2\text{CuO}_4$  films were prepared by an ultrasonic nebulization and pyrolysis method using acetylacetonates of the corresponding metals in alcohol solvents as source materials. Homogeneous, uniform films with good adherence have been obtained using this simple technique. As-deposited yttrium and lanthanum oxide films were poorly crystallized. After post-annealing in oxygen at higher temperature, they crystallized into cubic and hexagonal phases, respectively. Transparent yttrium and lanthanum oxide films have high electric breakdown voltages. Single phase polycrystalline  $\text{La}_2\text{CuO}_4$  thin films were obtained from a source solution with a La:Cu ratio of 2:1.

## Introduction

Yttrium oxide and lanthanum oxide films are mechanically and chemically stable and have high electrical breakdown field strengths (1-3) as well as high dielectric constants (4-5). They are also optically transparent over large ranges from ultraviolet to infrared (6-7). These films have attracted particular attention for application in gate insulators of metal oxide semiconductor field effect transistors (MOSFET) (4), optical antireflection coatings (7), and protective coatings (8-9). Various fabrication techniques have been employed for the preparation of  $Y_2O_3$  films (1,4,8,10) and  $La_2O_3$  films (2,5) such as electron beam evaporation (4-5), sputtering and subsequent oxidation (1), spray pyrolysis (8) and chemical vapor deposition (CVD) (10).

Recently a novel ultrasonic nebulization and pyrolysis technique has been developed in this laboratory for the preparation of thin oxide films of high quality (11-12). This paper reports on the preparation of yttrium and lanthanum oxide thin films as well as lanthanum copper oxide thin films by this simple method. The structural, optical and electrical properties of the films are investigated.

## Experimental

**Precursor preparation.** Yttrium acetylacetonate was chosen as precursor for the preparation of yttrium oxide films. To 4.6 g of  $Y_2O_3$  (Johnson Matthey 99.99%) was added 34 ml of 6 M hydrochloric acid and 53 ml of distilled water. The solution was heated on a steam bath in a fume hood until the solution was

clear. Then, 6 M ammonium hydroxide was added to the solution dropwise until a precipitate appeared. At this point, 6 M hydrochloric acid was added to the solution dropwise until the precipitate dissolved. This solution was then immersed in an ice bath with constant stirring and 16 ml acetylacetone (Aldrich) and 16 ml of propylene oxide (Aldrich) were added. To the solution, 10 ml of concentrated ammonium hydroxide were added and a fluffy white precipitate was formed. The precipitate and solution were refrigerated overnight and filtered. The precipitate was rinsed with cold distilled water and hexane and air-dried. The crude product was vacuum-dried at room temperature at 0.05 mm Hg or lower. The content of Y(III) was determined by a back-titration method using Cu-EDTA in an acetate buffer with PAN (Fisher) as the indicator (13-14).

Lanthanum acetylacetonate was the precursor for the preparation of lanthanum oxide and lanthanum copper oxide films. A solution was prepared by dissolving 4.04 g of  $\text{La}_2\text{O}_3$  (Aesar 99.99%) in 14 ml of 6 M hydrochloric acid. This solution was immersed in an ice bath with constant stirring and 10 ml acetylacetone (Aldrich) and 10 ml of propylene oxide (Aldrich) were added. To this solution, 6 ml of concentrated ammonium hydroxide were added and a fluffy white precipitate was formed. The precipitate and solution were refrigerated overnight and filtered. Lanthanum acetylacetonate was recovered as described above for yttrium acetylacetonate.

Copper acetylacetonate was the precursor for the preparation of lanthanum copper oxide films. A solution was prepared by dissolving 3.41 g of  $\text{CuCl}_2 \cdot 2\text{H}_2\text{O}$  (Baker and Adamson) in 10 ml of methanol. This solution was immersed in an ice bath with constant stirring and 5 ml acetylacetone

(Aldrich) and 5 ml of propylene oxide (Aldrich) were added. The solution was kept in the ice bath for 10 minutes and a blue-violet precipitate was formed. Sufficient distilled water was added to the precipitate and solution to give a total volume of 200 ml and then refrigerated overnight and filtered. Then a similar procedure as described for the preparation of yttrium acetylacetonate was followed to obtain copper acetylacetonate.

**Thin Film Preparation.** Thin films of yttrium oxide, lanthanum oxide and lanthanum copper oxide have been prepared by an ultrasonic nebulization and pyrolysis technique developed in this laboratory (12). The acetylacetonates of the corresponding metals were used as precursors for the thin film preparation. The reactor used in this investigation is shown in Fig. 1 and was heated by means of a two-zone mirror furnace (Trans-Temp Co., Chelsea, MA). An alcohol solution of the precursor was nebulized by a commercial ultrasonic humidifier (Holmes Air) and was carried into the horizontal reactor by argon. The substrate was held perpendicular to the gas flow in the furnace by a silica holder which was rotated by a low speed motor to achieve best uniformity. Both the efficiency of the deposition and the uniformity of the films were affected by the deposition parameters used. For the best uniformity, 1 inch of the tip of the nozzle was bent upward at an angle of about 15°. Typical reaction conditions used in the film preparation are listed in Table 1. Both silicon and silica wafers were used as substrates. Cleaning of the silicon substrates was carried out just prior to the deposition according to the procedure described by Fournier et al. (15). Silica substrates were cleaned with hydrochloric acid, distilled water and semiconductor grade acetone prior to the deposition. All films were post annealed in flowing oxygen for 30 minutes.

5

**Film Characterization.** The thickness of the films on silicon substrates was determined by ellipsometry using a Rudolph Research Auto EL-II ellipsometer (16). The wavelength of the laser beam was 632.8 nm. Values of the two ellipsometric angles, delta and psi, were recorded and input to a Hewlett-Packard 9825A computer to calculate the thickness. Additional input parameters for this calculation were the real ( $n_s = 3.877$ ) and complex ( $k_s = 0.019$ ) values for the index of refraction of the silicon substrate, and a trial value ( $n_p = 1.91$ ) for the index of refraction of the  $\text{La}_2\text{O}_3$  and  $\text{Y}_2\text{O}_3$  films. The thickness of films deposited on silica substrates was obtained from the interference fringes in their optical spectra.

X-ray diffraction patterns of these films were obtained using a Philips diffractometer and monochromated high intensity  $\text{CuK}\alpha_1$  radiation ( $\lambda = 1.5405$  Å). Diffraction patterns were taken with a scan rate of  $1^\circ 2\theta/\text{min}$  over the range  $10^\circ < 2\theta < 80^\circ$ . In order to detect the presence of trace impurity phases in  $\text{La}_2\text{CuO}_4$  films, a step counting technique was used (17). Counts for 200 seconds were made over the ranges  $29.5^\circ < 2\theta < 30.5^\circ$  and  $38.5^\circ < 2\theta < 39.5^\circ$ . These are the positions of the major (101) and (111,200) diffraction peaks of  $\text{La}_2\text{O}_3$  and  $\text{CuO}$ , respectively. Five measurements were made at each angle.

The surface topography of the films was studied by scanning electron microscopy. Pictures were taken with a JEOL 840F Scanning Electron Microscope. Optical measurements of the films on silica substrates were performed using a Cary model 17 dual beam ratio recording spectrophotometer in



the range of 190 nm to 2500 nm. Measurements were made in the transmission mode.

Current-voltage measurements were performed to determine the DC breakdown voltage of yttrium oxide and lanthanum oxide thin films. The measurements were carried out with samples in an Au/oxide/Si configuration (12). Gold was evaporated through a mask to obtain an array of circular electrodes of area 1 mm<sup>2</sup> on the surface of the film. Contact to a gold dot electrode was obtained by touching a gold-tipped micromanipulator to the surface. Contacts to the silicon substrate (p-type with a resistivity of 1  $\Omega$ -cm) consisted of indium alloy (Indalloy 9, Indium Corporation of America) ultrasonically bonded to the back surface. The indium alloy contacts were checked for ohmic behavior before measurement of the current-voltage characteristic. The reported current-voltage behavior is that for the gold dot electrode made negative with respect to the substrate. The area measured ignores a 1 mm boundary along the substrate edge.

### Results and Discussion

Smooth and homogeneous thin films of yttrium oxide, lanthanum oxide and lanthanum copper oxide have been grown on both silicon and silica substrates using ultrasonic nebulization of acetylacetonate solutions, followed by pyrolysis. The films had good adherence to both substrates. They appeared uniform and shiny. Both yttrium and lanthanum oxide thin films had bright colors varying with the thickness. Such interference colors were also visible with thin lanthanum copper oxide films, although these films usually appeared darker due to the nature of the compound. For yttrium and lanthanum oxide

thin films on silicon substrates, the thickness was measured at different positions on the film with an ellipsometer. It was found that the thickness variation on a substrate of 1 x 1 cm was within 1% except near the very edge. The bright and uniform color of the films on both silicon and silica substrates also revealed that they were uniform.

The films which were prepared by the above method were analyzed by x-ray diffraction. In the diffraction pattern of an as-deposited yttrium oxide film of 0.5  $\mu\text{m}$  in thickness on (100) silicon, only a broad peak at  $29^\circ$  could be identified. This indicated that the as-deposited yttrium oxide film was poorly crystallized. After the film was annealed in oxygen at  $600^\circ\text{C}$  for 6 hours, all of the diffraction peaks could be indexed on the basis of a cubic yttrium oxide phase with (111) preferred orientation (18). No impurity phase could be found. Heitmann (7) has reported that as-deposited yttrium oxide films prepared by vacuum evaporation were amorphous but that a certain crystallization was detected in annealed films (2 hrs at  $400^\circ\text{C}$  in air). Frank et al. (8) have reported crystalline yttrium oxide films prepared by spray pyrolysis.

Singh (2) has reported the preparation of amorphous lanthanum oxide films by vacuum deposition. In this study, the diffraction pattern of an as-deposited lanthanum oxide film of 0.5  $\mu\text{m}$  on (100) silicon, only a weak broad peak at  $29\text{--}31.5^\circ$  could be identified. This indicated that the as-deposited lanthanum oxide film was poorly crystallized. After the film was annealed in oxygen at  $800^\circ\text{C}$  for 6 hrs, all the diffraction peaks corresponded to the reflections of a hexagonal lanthanum oxide phase (19). No impurity phase could be found.

In the preparation of lanthanum copper oxide films, reaction parameters influenced their composition. For a fixed deposition temperature, carrier gas flow rate and distance between substrate and nozzle, different La:Cu ratios in a mixed-source solution of lanthanum acetylacetonate and copper acetylacetonate were tested. X-ray diffraction patterns were taken from lanthanum copper oxide films of 0.5  $\mu\text{m}$  in thickness which had been annealed in air at 800°C for 6 hrs. Fig. 2 shows the x-ray diffraction pattern of a lanthanum copper oxide film prepared on (100) silicon from a source solution with a La:Cu ratio of 2:1. The diffraction pattern of a standard sample of polycrystalline  $\text{La}_2\text{CuO}_4$  is also shown in Fig. 2. All the peaks in this pattern can be indexed on the basis of the face-centered orthorhombic unit cell of  $\text{La}_2\text{CuO}_4$  with cell parameters  $a = 5.400(2)$  Å,  $b = 13.14(1)$  Å, and  $c = 5.356(2)$  Å, in good agreement with the literature (17). Because the 0.5  $\mu\text{m}$  film was less well crystallized, its x-ray peaks were broader and some of the distinct peaks of  $\text{La}_2\text{CuO}_4$  remained unresolved.

Furthermore, a small amount of unreacted constituents might not appear as additional phases in the diffraction pattern of a thin film. Therefore, step counting was performed on these films over the range where lanthanum oxide and copper oxide have their strongest diffraction peaks. Films prepared from source solutions containing different lanthanum to copper ratios were analyzed. For the film prepared from a source solution with La:Cu = 2:1, there was no evidence of the presence of any detectable impurity phase. However, a trace amount of CuO appeared in the film prepared from a source solution with La:Cu = 1.8:1. A trace amount of  $\text{La}_2\text{O}_3$  appeared in the film prepared from a solution with La:Cu = 2.2:1. Hence, it was possible to

control the stoichiometry of such ternary oxide films by varying the ratio of the precursor concentrations in the source solution.

The prepared films were examined with scanning electron microscopy. They showed uniform grain textures. Fig. 3 shows a photomicrograph of an as-deposited lanthanum copper oxide film of  $0.3\text{ }\mu\text{m}$  thickness on silicon. The surface of the film showed a submicron grain texture with an average particle size of  $0.1 - 0.2\text{ }\mu\text{m}$ .

The UV, visible, and near-IR transmission spectra of as-prepared yttrium and lanthanum oxide films on silica are shown in Figs. 4 and 5, respectively. It can be observed in the spectra that the prepared yttrium and lanthanum oxide films are highly transparent over a large range from UV to near-IR.

Current-voltage measurements were made on as-deposited yttrium and lanthanum oxide films approximately  $0.2\text{ }\mu\text{m}$  thick in Au/Y<sub>2</sub>O<sub>3</sub>/Si and Au/La<sub>2</sub>O<sub>3</sub>/Si configurations, respectively. There was no observed voltage breakdown up to 18 V applied DC potential. These results demonstrate the formation of high-density films and are in agreement with those reported in the literature (1-2).

### Acknowledgments

This research received partial support from the Office of Naval Research, the National Science Foundation DMR 8803184 and the Eastman Kodak Company, Rochester, NY.

### References

1. L. Manchanda and M. Gurvitch, IEEE Electron Device Lett., 9, 180 (1988).
2. A. Singh, Thin Solid Films, 105, 163 (1983).
3. A. T. Fromhold, Jr., and W. D. Foster, Electrocomponent Sci. Technol., 3, 51 (1976).
4. T. S. Kalkur, R. Y. Kwor and C. A. Paz de Araujo, Thin Solid Films, 170, 185 (1989).
5. T. Mahalingam, M. Radhakrishnan and C. Balasubramanian Thin Solid Films, 78, 229 (1981).
6. G. Hass, J. B. Ramsey and R. Thun, J. Opt. Soc. Am., 49, 116 (1959).
7. W. Heitmann, Appl. Opt., 12, 394 (1973).
8. B. Frank and R. Groth, Thin Solid Films, 3, 41 (1969).
9. B. Gudmundsson and B. E. Jacobson, Thin Solid Films, 173, 99 (1989).

10. K. Kamata, S. Matsumoto and Y. Shibata, *Yogyo-Kyokai-Shi*, 90, 46 (1982).
11. W. DeSisto, M. Sosnowski, F. Smith, J. DeLuca, R. Kershaw, K. Dwight and A. Wold, *Mat. Res. Bull.*, 24, 753 (1989).
12. P. Wu, Y-M. Gao, R. Kershaw, K. Dwight and A. Wold, *Mat. Res. Bull.*, 25, 357 (1990).
13. M. M. Woyski and R. E. Harris, in "Treatise on Analytical Chemistry, Part II" (I. M. Kolthoff and P. J. Elving, Eds.), Vol. 8, p. 56, Interscience Publishers, New York (1963).
14. C. N. Reilley, R. W. Schmid and D. W. Lamson, *Analytical Chemistry*, 30, 953 (1958).
15. J. Fournier, W. DeSisto, R. Brusasco, M. Sosnowski, R. Kershaw, J. Baglio, K. Dwight and A. Wold, *Mat. Res. Bull.*, 23, 31 (1988).
16. R. Brusasco, R. Kershaw, J. Baglio, K. Dwight and A. Wold, *Mat. Res. Bull.*, 21, 301 (1986).
17. J. DiCarlo, C-M. Niu, K. Dwight and A. Wold, in "Chemistry of High-Temperature Superconductors II"; (David L. Nelson and Thomas F. George, Eds.), ACS Symposium Series No. 377, pp. 140-144, American Chemical Society, Washington, D.C. (1988).
18. JCPDS 25-1200.
19. JCPDS 5-602.

## Figure Caption Sheet

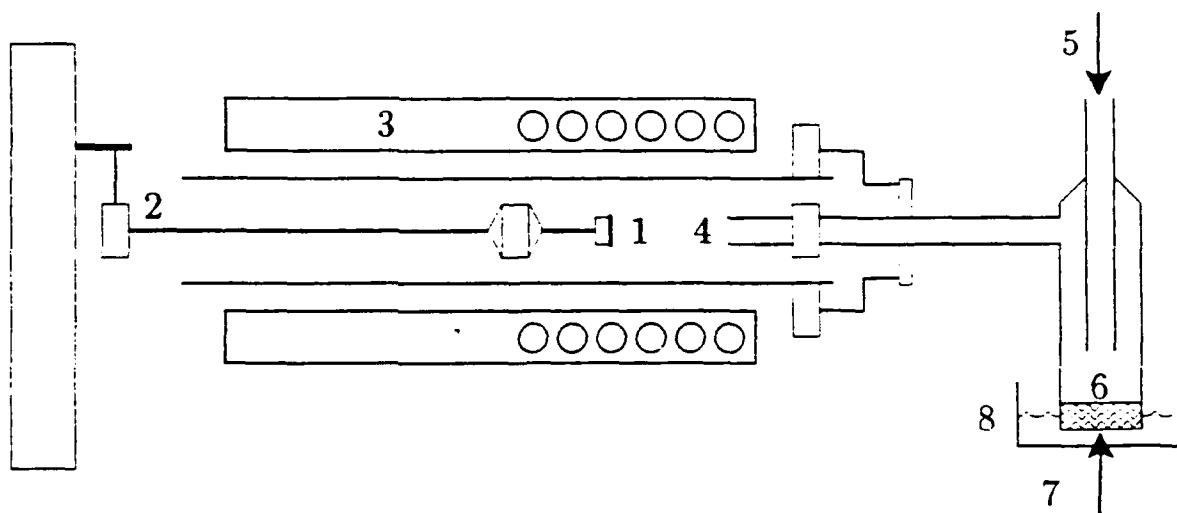
- Fig. 1. Schematic diagram of the deposition apparatus.
- Fig. 2. X-ray diffraction patterns of a) a 0.5  $\mu\text{m}$  film of  $\text{La}_2\text{CuO}_4$  and b) a polycrystalline standard sample of  $\text{La}_2\text{CuO}_4$ .
- Fig. 3. Photomicrograph of a typical lanthanum copper oxide film of 0.3  $\mu\text{m}$  thickness.
- Fig. 4. Transmission spectrum of a typical  $\text{Y}_2\text{O}_3$  film on silica.
- Fig. 5. Transmission spectrum of a typical  $\text{La}_2\text{O}_3$  film on silica.

Table 1

## Reaction Parameters

Thin Films	$\text{Y}_2\text{O}_3$	$\text{La}_2\text{O}_3$	$\text{La}_2\text{CuO}_4$
Precursor	$\text{Y}(\text{acac})_3$	$\text{La}(\text{acac})_3$	$\text{La}(\text{acac})_3$ 0.01 M
Concentration	0.01 M	0.01M	$\text{Cu}(\text{acac})_2$ 0.005 M
Solvent	Ethanol	Ethanol	Methanol
Deposition temperature	400°C	400°C	550°C
Substrate to nozzle distance	9 cm	9 cm	10.2 cm
Argon flow rate	3.7 l/min	3.7 l/min	4.1 l/min
Post anneal temperature	500°C	500°C	600°C

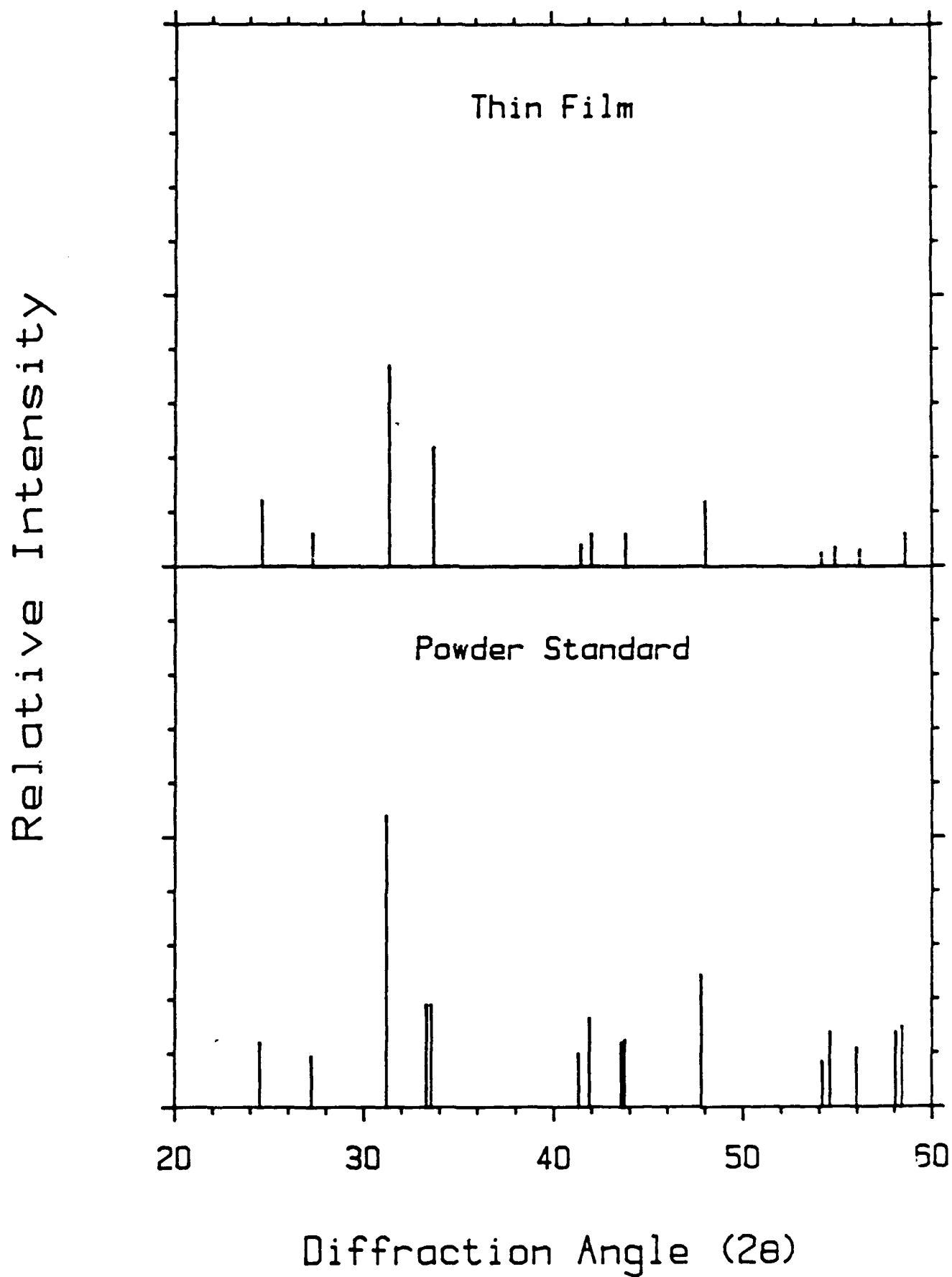


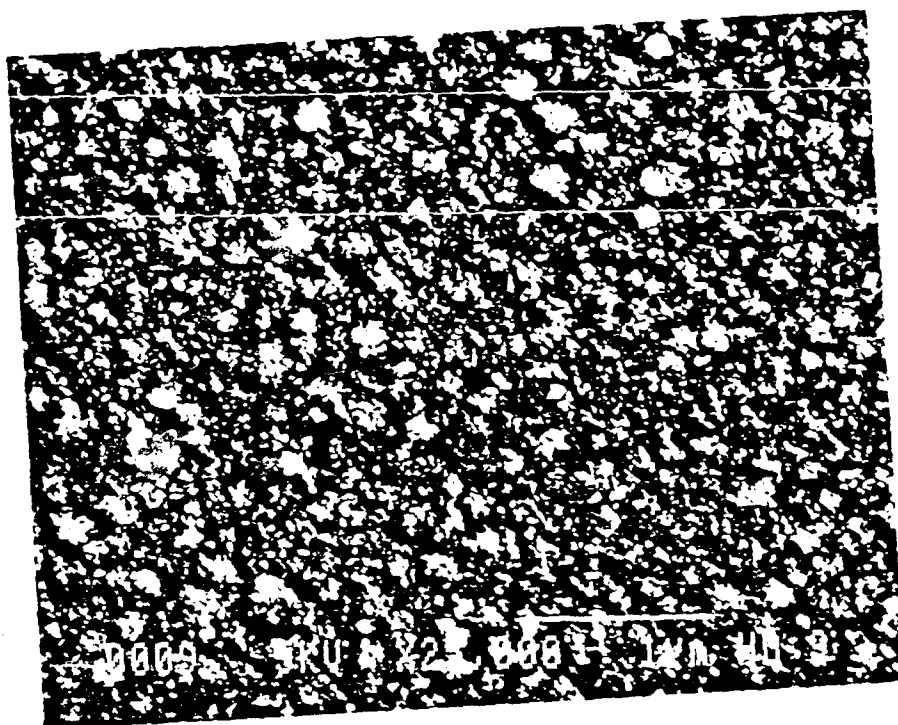


- 1 Substrate
- 2 Substrate rotation motor
- 3 Furnace
- 4 Spray nozzle

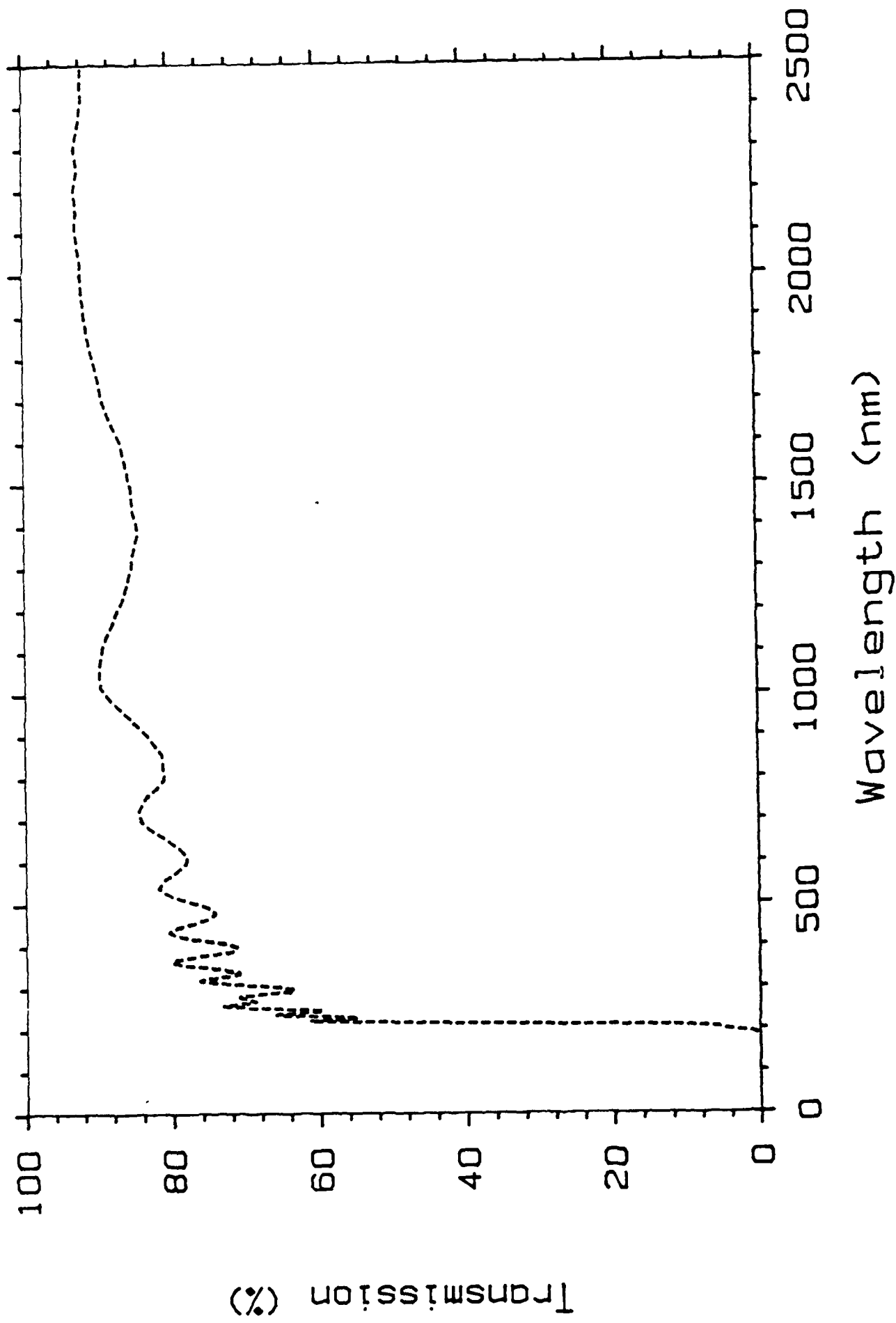
- 5 Carrier gas
- 6 Solution
- 7 Membrane
- 8 Ultrasonic Humidifier

# X-ray Analysis of $\text{La}_2\text{CuO}_4$





# Spectrum of $\text{Y}_2\text{O}_3$ on $\text{SiO}_2$



Spectrum of  $\text{La}_2\text{O}_3$  on  $\text{SiO}_2$

